Remarks:

Reconsideration of the application is requested.

Please charge any fees, which might be due with respect to Sections 1.16 and 1.17 to the Deposit Account of Lerner and Greenberg, P.A., No. 12-1099.

Respectfully submitted,

For Applicants

LAURENCE A. GREENBERC REG. NO. 29,308

August 29, 2001

Lerner and Greenberg, P.A. Post Office Box 2480 Hollywood, FL 33022-2480

Tel: (954) 925-1100 Fax: (954) 925-1101

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Abstract:

On page 29, the following changes were made in the first paragraph:

A vertically structured semiconductor power [module] <u>component</u> is described. A layer thickness of a substrate of the power module between a pn junction and a metallized back is chosen in such a manner that a space charge region produced in the semiconductor [module] <u>component</u> extends as far as the back when a blocking voltage between a source and a drain electrode is applied before a field strength produced by the applied blocking voltage reaches a critical value.